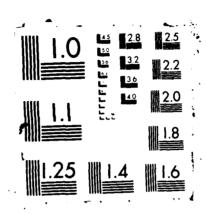
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Sehun Kim and R. Stanley Williams

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Semiempirical band structure of PtGa₂

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A semiempirical band structure for PtGa₂ was obtained by adjusting the AuGa₂ parameters in the mixed-basis band-structure interpolation scheme to obtain agreement between the calculated total density of states (DOS) and x-ray photoemission spectroscopy data. Angle-resolved photoemission spectroscopy data collected from a PtGa₂ (111) surface with a noble-gas-discharge lamp as excitation source were used to check the energies of the d bands. The PtGa₂ band structure is compared to those of both elemental Pt and Au, and the gold color of PtGa₂ is explained in terms of its Au-like DOS.

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I. INTRODUCTION

The study of the electronic structure of materials has been an intense field of research in the past two decades. During this time the experimental theoretical methods available have become increasingly sophisticated. Elemental metal such as Ag have been examined in great detail, and the agreement between recent band-structure calculations and angle-resolved photoelectron spectroscopy (ARPES) data² for this system is excellent. However, determining the band structure of a compound is far more challenging. The increased number of atoms in the primitive unit cell makes ab initio calculations much more difficult, and there are thousands of compounds (mostly intermetallic compound) composed of just two elements. The likelihood that a band structure has been calculated for an arbitrary compound is very small, and thus reliance on experimental determinations and semiempirical calculations of valence-band structures will probably increase as the materials community investigates new classes of compounds.

Binary intermetallic compounds that contain a transition metal and a group-III metal are interesting from both technological and academic points of view. For instance, conducting contacts of AuGa₂ are thermodynamically more stable than elemental Au on GaSb (Ref. 3) and GaAs (Ref. 4), and thus the electronic and magnetic properties of this and related intermetallic compounds may be important in circuitry. Such compounds are also excellent systems for studying d bands, since the group-III metals contribute only s-p states to the valence band. This makes is possible to examine the effects of structure and chemical bonding on d states in the compounds. The primary concern of this paper is the effect of the Ga

valence states on the d states of Pt in PtGa₂.

The only ab initio band structures for compounds similar to PtGa2 are those for the structurally related compounds AuAl2, AuGa2, and AuIn2, which were calculated by Switendick and Narath⁵ in 1968. That calculation ignored spin-orbit splitting effects and used a rather small basis set. We have recently refined Switendick's band structures of AuGa2 and AuIn2 by the use of a combination of data from x-ray photoelectron spectroscopy (XPS) (Ref. 6) and ARPES (Ref. 7) to revise the parameters that were initially fitted to the ab initio band structures in a mixed-basis band-structure interpolation scheme (MBBSIS).8 The MBBSIS, which was based on that developed by Smith, may then be used to compute the full E versus k dispersion relations for the bands, calculate total or orbital-symmetry-projected density of states (DOS), 10 or even plot out approximate charge densities 11 to obtain a bond picture of the compounds.

Several interesting features were noted in the semiempirical band structures of $AuGa_2$ and $AuIn_2$.^{7.8} The apparent width of the d bands of the two compounds was narrower than those of elemental Au, even though the relative splitting of the three d states at Γ of the Brillouin zone (BZ) for Au, $AuGa_2$, and $AuIn_2$ was nearly identical. Thus the crystal-field effects appeared to be similar for all three materials; the narrowing of the d bands of the intermetallic compounds resulted primarily from the fact that they appeared in a band gap of the s-p states and thus hybridized only weakly with strongly dispersing bands.

The present study of the valence bands of PtGa₂ was initiated to gain additional insight into the d-band structure of intermetallic compounds. The crystal structure of PtGa₂ is cubic fluorite, the same as AuGa₂ and AuIn₂, and the lattice constant is 5.911 Å, which is slightly

smaller than that of AuGa₂ (6.063 Å).¹² PtGa₂ is a gold-colored compound, so its electronic structure should resemble that of Au. No previous band structure of PtGa₂ existed, so the MBBSIS band structure of AuGa₂ was adjusted to provide agreement between the MBBSIS DOS and XPS data for PtGa₂. ARPES data collected from a PtGa₂ (111) surface with a noble-gas-discharge lamp as the excitation source were used to check the energies of the d bands.

Section II of this paper describes the experimental procedure. In Sec. III the experimental data and the semiempirical band structure are presented and discussed. The conclusions of this work are contained in Sec. IV.

II. EXPERIMENTAL PROCEDURE

A single crystal¹³ of PtGa₂ was oriented using Laue x-ray diffractometry, and then was cut by a wire saw to reveal a (111) surface. The PtGa₂ sample was mounted on a polishing fixture, reoriented to within 1° of the (111) plane by Laue photography, and polished to mirror smoothness using 0.5-, 0.3-, and 0.05-mm alumina grit. The crystal was etched for about two minutes in awua regia, and degreased with acetone and methanol before it was mounted in either the XPS or the ARPES chambers.

The XPS data for PtGa2 were collected with a vacuum generators Escalab equipped with a nonmonochromatic Mg $K\alpha$ (hv = 1253.6 eV) x-ray source. The sample was cleaned by several cycles of sputtering with Ar ions and annealing until the XPS spectra showed that the O and C contamination of the surface was negligible. The valence-band spectra were collected overnight, and subsequent core-level spectra showed that the surface contamination during the data accumulation was also negligible. Since low-energy electron diffraction (LEED) and Auger measurements were not available in the present ARPES chamber for this experimental, a cleaning procedure similar to that described above was used. Alternating cycles of argon-ion bombardment and annealing to 825 K were done for two days, and a final cleaning cycle was performed just prior to data acquisition. The ARPES spectra were free of any obvious contamination by O or C, but the spectra were broad and contained contributions from several different emission lines. These proved to be a major nuisance, since intense emission from the Ga 3d states, photoexcited by a high-energy satellite, often interfered with the valence spectrum corresponding to one of the primary emission lines.

The photoelectrons were collected with a 160° hemispherical electrostatic energy analyzer. The noble-gas-discharge lamp was operated with He, Ne, and Ar to provide various photo energies (Ar I; 11.6; Ne I, 16.9; Ne II, 26.9; He I, 21.2; and He II, 40.8 eV). The angle of incidence of the light with respect to the sample surface was 52.5°. Typical photoelectron intensities at normal emission for most of the lines were about 2×10^4 counts/sec except for the He II line, for which the count rate was 6×10^2 counts/sec. The analyzer was operated in a constant-pass energy mode with a resolution of approximately 0.3 eV.

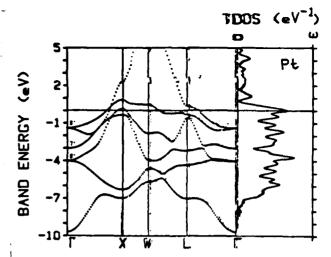


FIG. 1. Band structure and TDOS of Pt raisonlated using the 16-plane-wave MBBSIS. The parameters were fated to the first-principles calculation of Ref. 14. The energy scale is referenced to the Fermi energy and the TDOS scale is in electrons of two spins per eV per unit cell volume.

III. RESULTS AND DISCUSSION

The energy bands and total DOS (TDOS), calculated using Smith's interpolation scheme with 16 plane waves in the basis set, are presented for Pt and Au in Figs. 1 and 2, respectively, for comparison with those of PtGA₂. Although the parameters for Smith's pressures interpolation scheme, with 4 plane waves in the basis set, were available for Pt from Ref. 14, they were revised to be consistent with the 16-plane-wave interpolation scheme. The band structure of Pt in Fig. 1 was obtained by fitting the MBBSIS parameters to the first-principles calculation of Anderson, which agreed very well with the ARPES data of Ref. 16. The spin-orbit parameter (\$\subseteq = 0.59\$), to determined from the spirings of the d bands at \$\Gamma\$ from the first-principles calculation of Anderson.

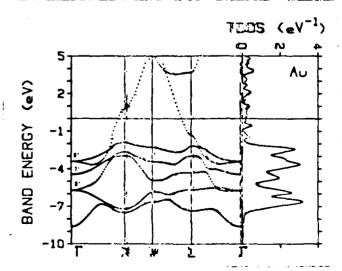


FIG. 2. Band structure and TDDS of Xii calculated using the 16-plane-wave MBES15 and the primarieties of Ref. 9.

to provide a more precise agreement with Anderson's band structure. The Au band structure in Fig. 2 was calculated using the MBBSIS parameters published in Ref. 9. Figure 3 is the semiempirical band structure of PtGa₂, which was obtained by adjusting the MBBSIS parameters of AuGa₂ to optimize the agreement between the calculated total DOS and the XPS valence-band spectra for PtGA₂, as shown in Fig. 4. The experimental value for the spin-orbit parameter for elemental Pt (ξ =0.63 eV) (Ref. 14) was used in the MBBSIS for PtGa₂, since Ref. 7 showed that ξ for Au was nearly the same in both the elemental metal and in the intermetallic compounds AuGa₂ and AuIn₂.

Table I lists the MBBSIS parameters used to generate the energy bands and TDOS for Pt and PtGa₂. The MBBSIS with 16 plane waves in the basis set was used for the Pt energy bands, while the version with 39 plane waves was used for PtGa₂. Thus a direct comparison between Pt and PtGa₂ pseudopotential parameters may not be meaningful. However, the smaller values of the hy-

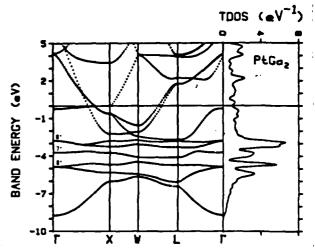


FIG. 3. Band structure and TDOS of PtGa₂. The 39 plane-wave MBBSIS parameters for AuGa₂ of Ref. 8 were adjusted to improve the agreement between the calculated TDOS and the XPS valence-band spectrum of PtGa₂.

TABLE I. MBBSIS parameters for Pt and PtGa₂ band structures. All values in eV except R in a reduced unit $(4a/\pi)$ and the lattice constant in Å. The \pm signs indicate the standard deviation of parameters. The parameters are intentionally reported with more significant figures than justified by the standard deviations in order to produce band structures that are essentially identical with those shown in Figs. 1-3. The MBBSIS employed for the Au and Pt band structures utilized 16 plane waves in the basis set, while that for PtGa₂ used 39 plane waves.

Parameters	Pt ^a	PtGa ₂ ^b	
E_0	8.368 ±0.2	2.288 ±0.2	
Δ	0.1334 ± 0.4	-0.2868 ± 0.5	
A_1	0.2383 ± 0.1	0.0423 ± 0.1	
A:	0.0137 ± 0.07	-0.0119 ± 0.07	
A_{λ}	-0.0556 ± 0.1	0.0570 ± 0.2	
A4	-0.0419 ± 0.1	0.0561 ± 0.1	
A_{Σ}	0.0413 ± 0.08	-0.0507 ± 0.08	
An	- 0.1283±0.1	0.0373 ± 0.1	
5	8.21 ±6	6.68 ± 2	
B :	36.99 ± 2	8.42 ± 2	
B .	37.45 ± 3	4.56 ± 5	
α	0.2008 ± 0.004	0.0607 = 0.001	
R	0.3127 ± 0.01	0.2535± 0.02	
$V_{(00)}$	-0.7663 ± 0.3	0.1424 ± 0.2	
V_{111}	0.0123 ± 0.4	2.564 ± 0.2	
V ₂₀₀	0.5956±0.6	3.707 ± 0.2	
V 220	3.946 ± 0.6	1.972 ±0.2	
V ₃₁₁	2.402 ±0.6	1.769 - 0.2	
V ₂₂₂	2.565 ± 0.6	1.275 ± 0.3	
	0.59	0.63	
ξ E _f °	8.90	5.55	
Lattice			
constants	3.92	5.911	
Average			
deviation	0.15	d	

^{*}Parameters were fitted to first-principles results of Ref. 15 using 16 plane waves in the basis set. The spin-orbit parameter ξ was taken from Ref. 16.

^bParameters were empirically adjusted to improve the agreement between the calculated total DOS and XPS data. The experimental value of the spin-orbit parameter ξ of Pt taken from Ref. 14 was used for that of PtGa₂.

^{&#}x27;Taken from Ref. 14 for Pt. The value for PtGa₂ was determined from the DOS calculation. These offsets are used to define the Fermi energy as the zero of the energy scale for each band structure.

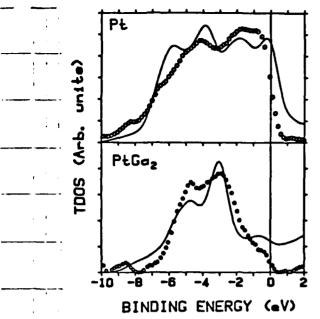


FIG. 4. Comparison between the XPS spectra (circles) with a piecewise linear background subtracted and the calculated TDOS (solid line) with 1.0 eV Gaussian broadening for Pt and PtGa₂. The curves are plotted vs binding energy referenced to the Fermi energy. The calculated curve shows both the occupied and unoccupied DOS. There is a striking similarity between the XPS valence-band spectra of PtGa₂ and Au.

bridization parameters B_t and B_c of PtGa₂ compared to those of Au and Pt indicate less hybridization of the d bands with the other bands, as observed previously in the case of the Au intermetallic compounds.⁸

In the earlier study of Au, AuGa2, and AuIn2, the width of the d density of states for the Au intermetallic compounds was much narrower than for elemental Au, even though the d band splitting at Γ was nearly identical for all three materials. This was taken as evidence that the crystal-field effects were similar in all three materials, despite the fact that the Au-Au distance varied drastically. The narrowing of the d bands of the compounds resulted primarily from the fact that they reside within a band gap of the s-p bands and thus hybridize only weakly with the highly dispersing bands. By comparing energy bands and TDOS for Pt and PtGa2 in Figs. 1 and 3, one can see that the d band splitting at Γ for Pt (2.7 eV) is 35% larger than for PtGa₂ (2.1 eV), and thus there appears to be some effect of the Pt-Pt distances on the relative widths of the d bands in Pt and PtGa2. The total dband width for elemental Pt is twice that of PtGa2, however, as can be seen in the comparison of the XPS valence-band spectra and TDOS calculations in Fig. 4. For a more complete discussion of the difference contributions to the total bandwidth, see Ref. 8. The same reasoning discussed for Au and AuGas can be applied to the case of Pt and PtGay. The dimensions of the BZ for PtGa₂ are smaller than for Pt, since the lattice constant of PtGa₂ is much larger than that of Pt. Thus the strongly dispersing s-p band reaches the BZ boundary before it can cross the 5d bands, as shown in Fig. 3. Therefore, the d bands of PtGa₂ appear in a band gap of the s-p band⁵ and hybridize only weakly with the strongly dispersing bands, while elemental Pt d bands mix strongly with an s-p band and create a broad TDOS.

An XPS valence-band spectrum represents an experimental density of states of the valence bands that is weighted by the photoionization cross sections of the various components within the valence band. Thus XPS spectra can be used to test band-structure calculations. In Fig. 4 the XPS spectra of Pt and PtGa2 are compared with the TDOS calculated by the MBBSIS. The TDOS was calculated at 60 special k points 18 with a 1.0-eV Gaussian broadening to simulate the experimental resolutions and intrinsic broadening effects. The agreement between the TDOS calculations and the XPS spectra is reasonably good, except for the relative intensities of the features in the spectra. The first peak at -3 eV in the calculated TDOS of PtGa2 shows a higher density of states than the second peak at -5 eV, while the two peaks in the XPS spectrum are comparable. This probably results from the fact that the upper three d bands of Γ_8 and Γ_7 symmetry are flat bands in the MBBSIS, and show less dispersion across the BZ than that of the lower two d bands of Γ_8 symmetry. The small feature at -8.5eV in the XPS spectrum was caused by the Mg $K\alpha_{34}$ satellite x-ray line. The bandwidth at half maximum of the XPS spectrum for PtGa₂ (3.9 eV) was larger than for AuGa₂ (3.2 eV).8

Figure 5 presents the normal-emission ARPES spectra of the PtGa₂ (111) surface at different photon energies us-

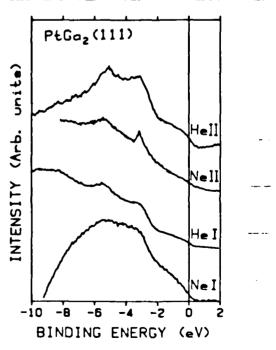


FIG. 5. ARPES spectra at normal emission for $P(Ga_2, \{11\})$ collected using a noble-gas-discharge lamp as the excitation source. The two primary features observed in each spectrum correspond to the two $\Gamma_{\rm p}$, bands of $P(Ga_2)$, and essentially no dispersion of these two bands across the Λ direction of the BZ is detected, in agreement with the band structure of Fig. 3.

energetically closer together at Γ in PtGa₂ than in AuGa₂. The band structures of Figs. 1-3 show why Pt is silver colored and PtGa₂ is gold colored. The Pt DOS is relatively high across the entire region from 1 to 4 eV binding energy, so that the absorption of light by Pt is fairly constant over the entire visible range of the electromagnetic spectrum. For Au and PtGa₂, however, an s-p plateau with a fairly low DOS extends from 0-2 eV binding energy, whereas at higher binding energies there is a very high d DOS. Thus the PtGa₂ DOS looks very similar to that of Au, and their color arises from the fact that blue and violet light are absorbed much more strongly than yellow and red light. The shape of the PtGa₂ DOS can be understood by considering the fact that elemental Ga has a

work function of 4.2 eV¹⁹ whereas that for Pt is 5.7 eV.¹⁹ Adding the s-p DOS of Ga to the Pt DOS, with the vacuum levels of the two elements in common, would yield a picture qualitatively similar to the PtGa₂ DOS in Fig. 3. Since the Pt d states are below the, Fermi level of the compound, they are completely filled, and the total d band width of the compound is narrower than that for elemental Pt for the reasons discussed previously

IV. CONCLUSIONS

A semiempirical band structure of PtGa₂ was obtained by adjusting the MBBSIS parameters of AuGa₂ to improve the agreement between the calculated total DOS and XPS data for PtGa₂. The d-band width of PtGa₂ was much narrower than that of Pt, since the d bands reside in a band gap of the s-p bands and thus hybridize weakly with the s-p bands. The gold color PtGa₂ arises from the preferential absorption of blue and violet light caused by the abrupt increase of the DOS at a binding energy of 2 eV, which is also a feature of the Au DOS.

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